



40V PNP HIGH GAIN LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

Features

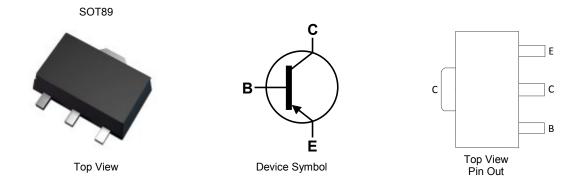
- BV_{CEO} > -40V
- I_C = -5.5A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -30mV @ -100mA
- R_{sat} = 29mΩ for a Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.05 grams (Approximate)

Application

- DC-DC converters
- MOSFET gate drive
- Charging circuits
- Power switches
- Motor control



Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTP2009ZTA	Standard	53Z	7	12	1,000

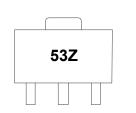
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



53Z = Product Type Marking Code



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Base Voltage	V _{CBS}	-50	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-7.5	V
Continuous Collector Current	lc	-5.5	A
Peak Pulse Collector Current (single pulse)	Ісм	-15	A

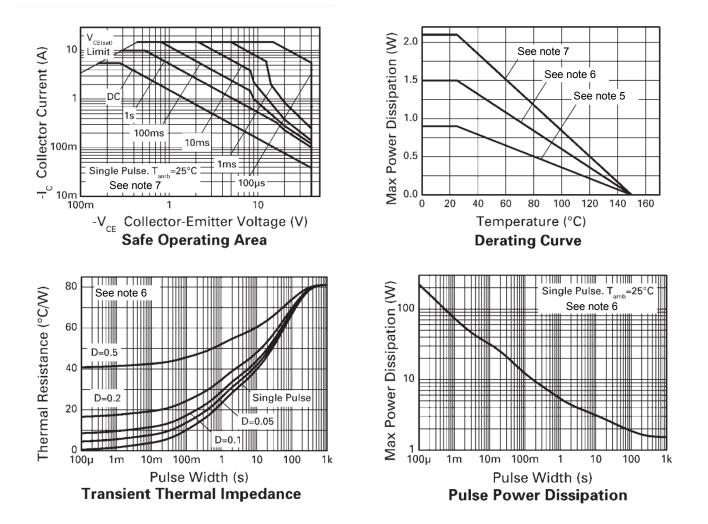
Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	PD	0.9 7.2	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	PD	1.5 12	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	PD	2.1 16.8	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	PD	3 24	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	139	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	83	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{0JA}	60	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R _{θJA}	42	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

 For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.
Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.
Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.
Same as note (5), except the device is measured at t<5 seconds. Notes:



Thermal Characteristics and Derating Information





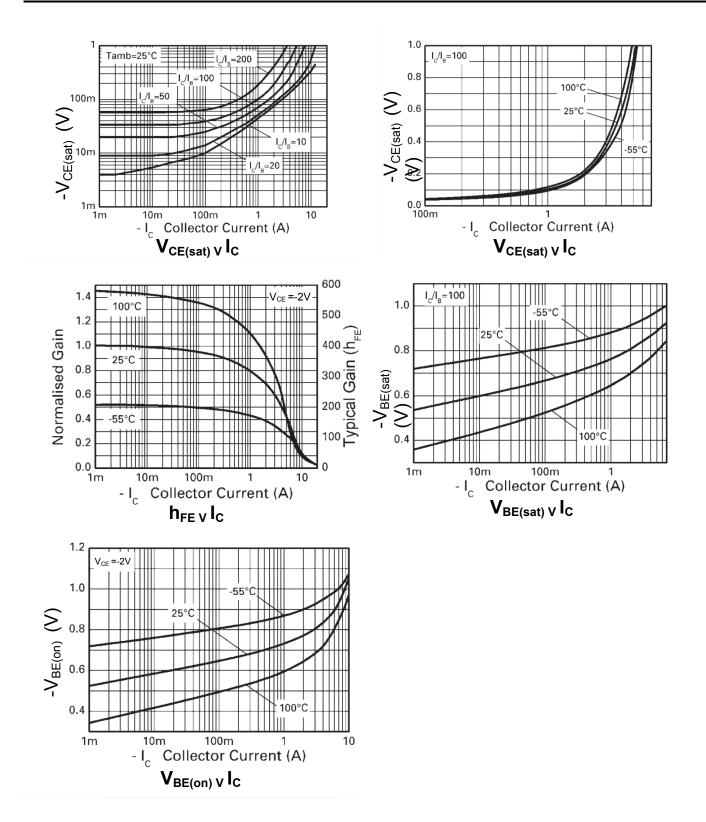
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV CBO	-50	-90	_	V	I _C = -100μΑ
Collector-Emitter Breakdown Voltage	BV _{CES}	-50	-90	_	V	I _C = -100μΑ
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-40	-58	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7.5	-8.3	_	V	I _C = -100μΑ
Collector-Base Cut-Off Current	I _{CBO}	_	-1	-20	nA	V _{CB} = -40V
Collector-Emitter Cut-Off Current	I _{CES}		-1	-20	nA	V _{CB} = -32V
Emitter-Base Cut-Off Current	I _{EBO}		-1	-20	nA	V _{EB} = -6V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	_	-15 -44 -50 -120 -70 -125 -130 -162	-30 -60 -70 -165 -80 -175 -175 -185	mV	$\begin{split} I_{C} &= -0.1A, \ I_{B} &= -10mA \\ I_{C} &= -1A, \ I_{B} &= -100mA \\ I_{C} &= -1A, \ I_{B} &= -50mA \\ I_{C} &= -1A, \ I_{B} &= -10mA \\ I_{C} &= -2A, \ I_{B} &= -10mA \\ I_{C} &= -2A, \ I_{B} &= -200mA \\ I_{C} &= -2A, \ I_{B} &= -40mA \\ I_{C} &= -3.5A, \ I_{B} &= -175mA \\ I_{C} &= -5.5A, \ I_{B} &= -550mA \end{split}$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	-820 -1000	-900 -1075	mV	I _C =-2A, I _B =-40mA I _C =-5.5A, I _B =-550mA
Base-Emitter Turn-On Voltage (Note 9)	$V_{\text{BE(on)}}$	_	-778 -869	-850 -950	mV	I _C =-2A, V _{CE} =-2V I _C =-5.5A, V _{CE} =-2V
DC Current Gain (Note 9)	hfe	200 200 175 110	390 350 290 175	 550 	_	$I_{C} = -10 \text{mA}, V_{CE} = -2V$ $I_{C} = -0.5\text{A}, V_{CE} = -2V$ $I_{C} = -2\text{A}, V_{CE} = -2V$ $I_{C} = -5.5\text{A}, V_{CE} = -2V$
Transitional frequency	f _T	_	152	_	MHz	$I_{C} = -50 \text{mA}, V_{CE} = -10 \text{V},$ f = 100MHz
Output Capacitance	C _{obo}	—	53	_	pF	V _{CB} = -10V, f = 1MHz
	t _d		18		ns	I _C =-1A, V _{CC} =-10V,
Switching times	tr		17			
	ts		325	— 115	I _{B1} =-I _{B2} =-100mA	
	t _f		60			
	td		55			
	tr	107			I _C =-2A, V _{CC} =-30V,	
Switching times	ts		264	—	ns	$I_{B1} = -I_{B2} = -20 \text{mA}$
1	tf	1	103	1		

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



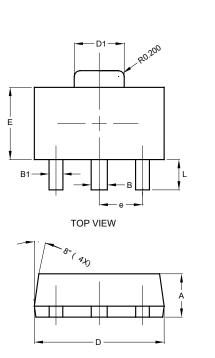
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

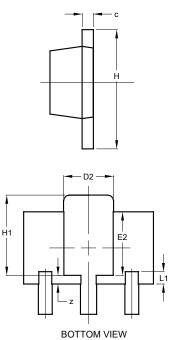




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

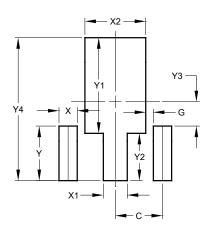




SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
z	0.20	0.40	0.30		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)	
С	1.500	
G	0.244	
Х	0.580	
X1	0.760	
X2	1.933	
Y	1.730	
Y1	3.030	
Y2	1.500	
Y3	0.770	
Y4	4.530	

st version.

SOT89



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